

PBSS4021NZ

20 V, 8 A NPN low V_{CEsat} (BISS) transistor Rev. 01 — 31 March 2010

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PZ.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	8	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	20	Α
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = 6 \text{ A};$ $I_{B} = 600 \text{ mA}$	<u>[1]</u> _	14	20	mΩ

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 2. Pinning

100.0 2.	9		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector	4	2, 4
3	emitter		1 —
4	collector		. ,
			3 sym016
			syllioto

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4021NZ	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

3	
Type number	Marking code
PBSS4021NZ	PB4021NZ

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

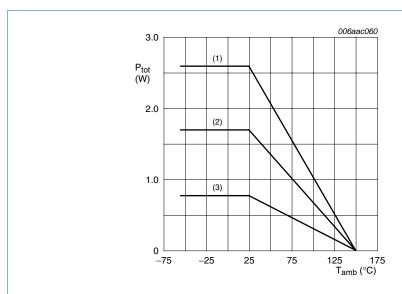
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	20	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	8	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	20	Α
I _B	base current		-	1	Α

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	770	mW
			[2] _	1700	mW
			[3] _	2600	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

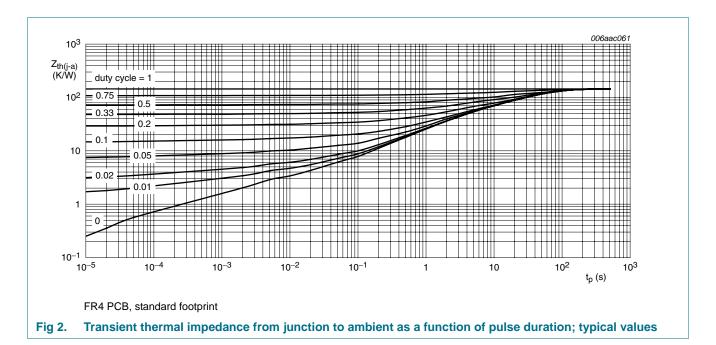
Fig 1. Power derating curves

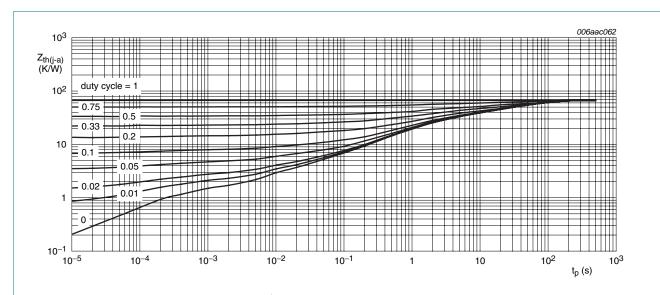
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> -	-	160	K/W
junction to ambient	junction to ambient		[2] -	-	75	K/W
			<u>[3]</u> _	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	11	K/W

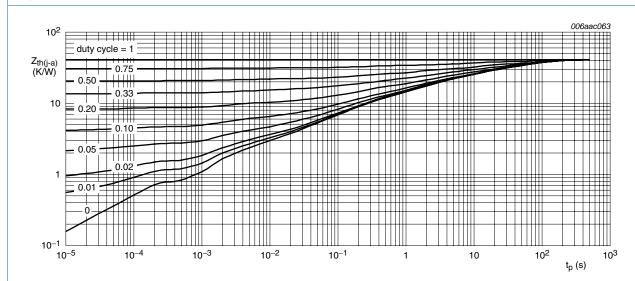
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





FR4 PCB, mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

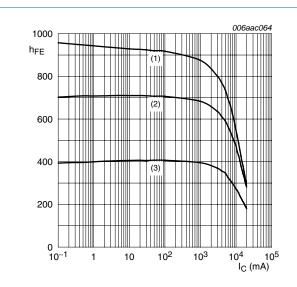
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
	current	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	50	μА
I _{CES}	collector-emitter cut-off current	$V_{CE} = 16 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain		[1]				
		V _{CE} = 2 V; I _C = 500 mA		300	550	-	
		V _{CE} = 2 V; I _C = 1 A		300	550	-	
		V _{CE} = 2 V; I _C = 2 A		300	500	-	
		V _{CE} = 2 V; I _C = 4 A		250	450	-	
		V _{CE} = 2 V; I _C = 8 A		250	400	-	
V_{CEsat}	collector-emitter		[1]				
	saturation voltage	$I_C = 1 A$; $I_B = 50 \text{ mA}$		-	18	30	mV
		I _C = 1 A; I _B = 10 mA		-	27	40	mV
		$I_C = 2 \text{ A}; I_B = 40 \text{ mA}$		-	37	55	mV
		$I_C = 4 \text{ A}; I_B = 200 \text{ mA}$		-	60	85	mV
		$I_C = 4 \text{ A}; I_B = 40 \text{ mA}$		-	75	105	mV
		I _C = 8 A; I _B = 400 mA		-	120	170	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = 6 \text{ A}; I_B = 600 \text{ mA}$	[1]	-	14	20	mΩ
V_{BEsat}	base-emitter	$I_C = 1 A; I_B = 100 \text{ mA}$	[1]	-	0.84	0.9	V
	saturation voltage	I _C = 4 A; I _B = 400 mA	[1]	-	0.98	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	[1]	-	0.72	0.85	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 1 \text{ A};$		-	60	-	ns
t _r	rise time	$I_{Bon} = 0.05 \text{ A};$ $I_{Boff} = -0.05 \text{ A}$		-	40	-	ns
t _{on}	turn-on time	IROII — _0.00 K		-	100	-	ns
ts	storage time			-	780	-	ns
t _f	fall time			-	80	-	ns
t _{off}	turn-off time			-	860	-	ns
f _T	transition frequency	$V_{CE} = 10 \text{ V};$ $I_{C} = 100 \text{ mA};$ f = 100 MHz		-	95	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	110	-	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



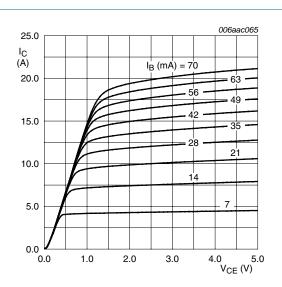
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

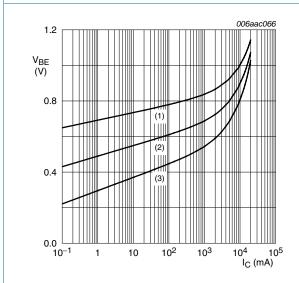
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 6. Collector current as a function of collector-emitter voltage; typical values



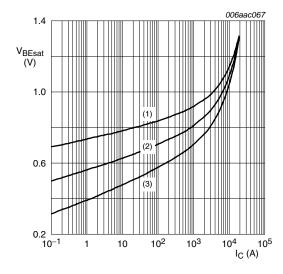


(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter voltage as a function of collector current; typical values



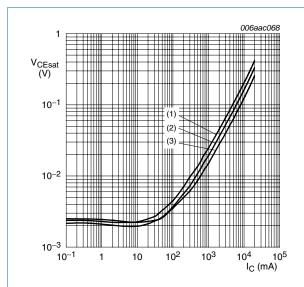
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



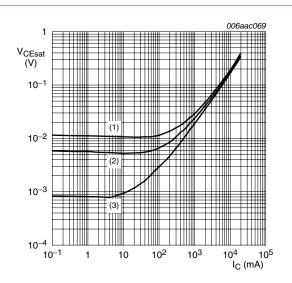
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



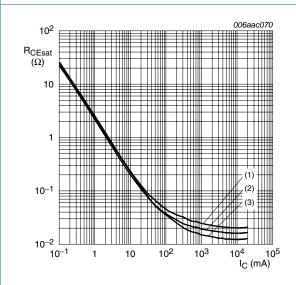
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



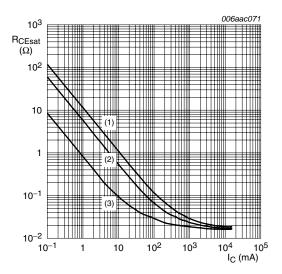
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



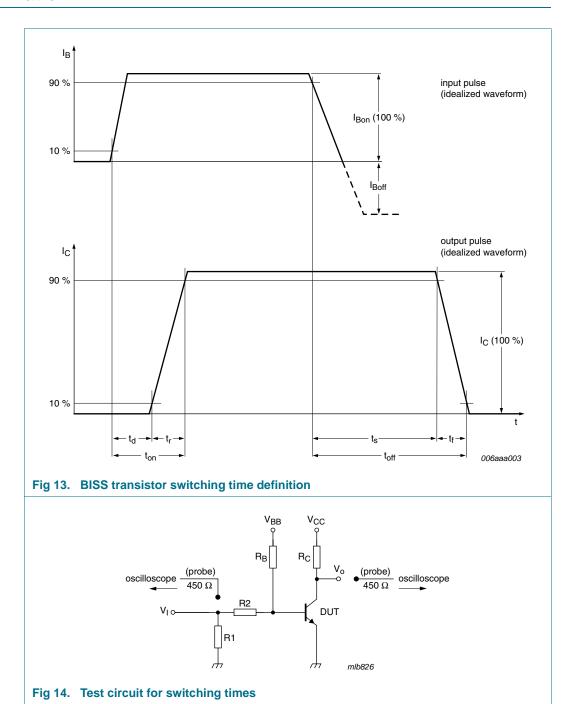
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

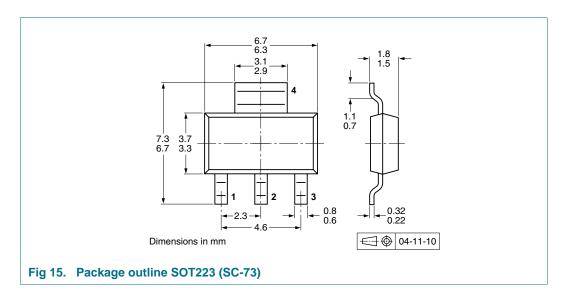
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

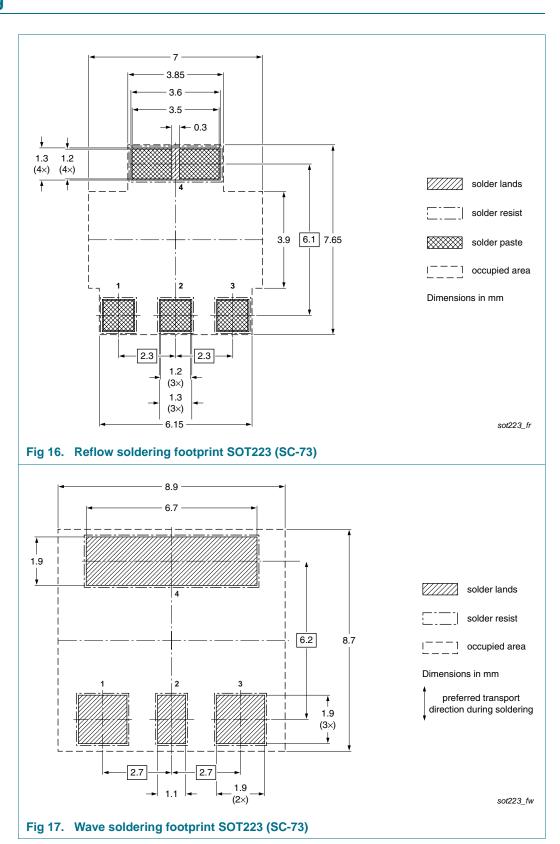
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	uantity
			1000	4000
PBSS4021NZ	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



Nexperia PBSS4021NZ

20 V, 8 A NPN low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NZ_1	20100331	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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20 V, 8 A NPN low V_{CEsat} (BISS) transistor

14. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: $\underline{\textbf{salesaddresses@nexperia.com}}$

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